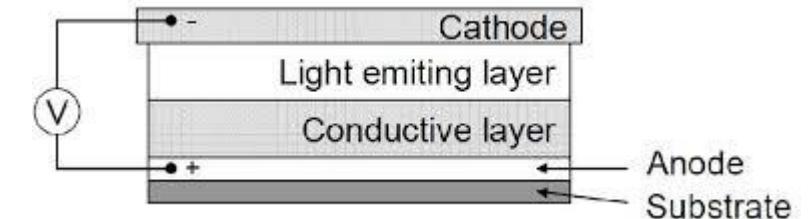
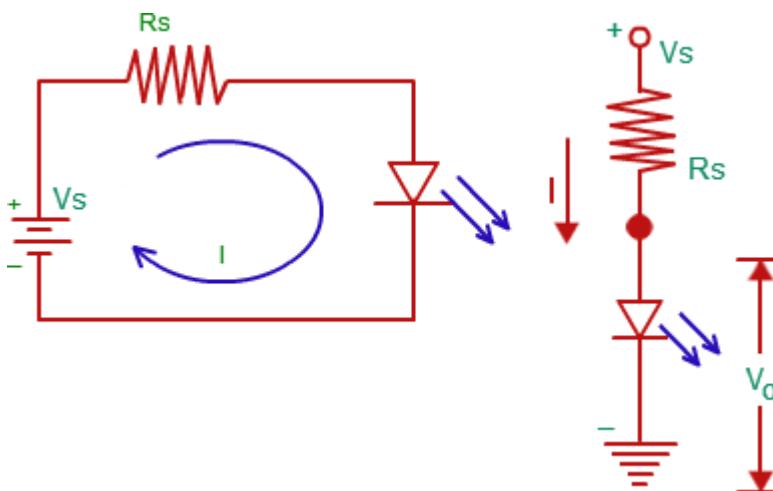
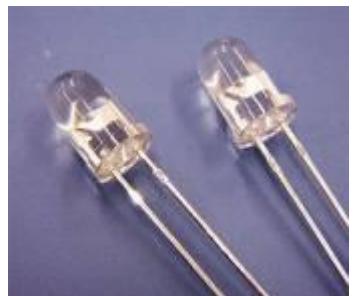


# Switchable diode in BiFeO<sub>3</sub>

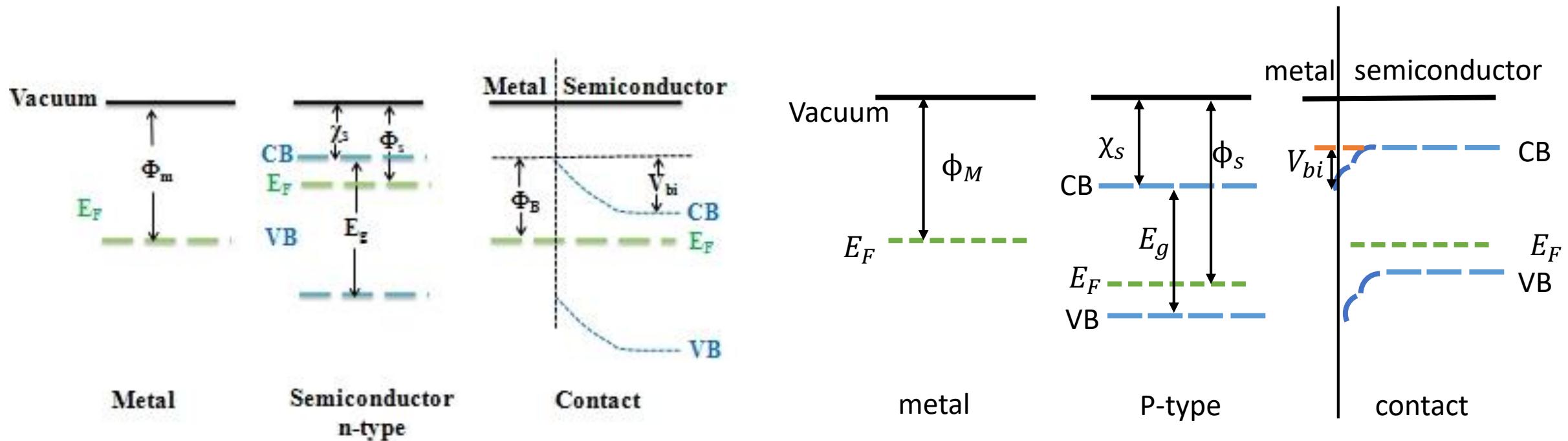
Xuanyuan Jiang

2018/04/20

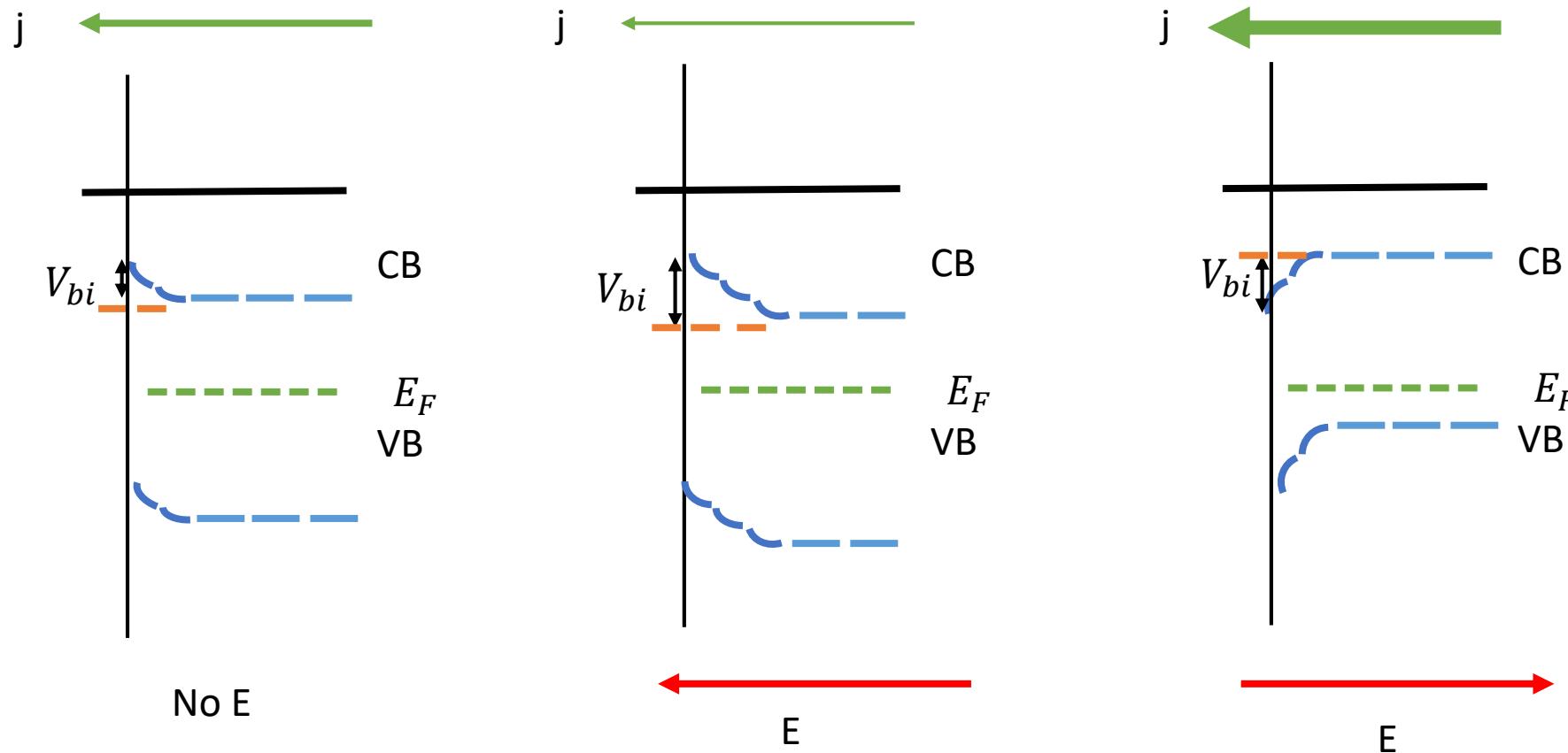
# Light emitter diode



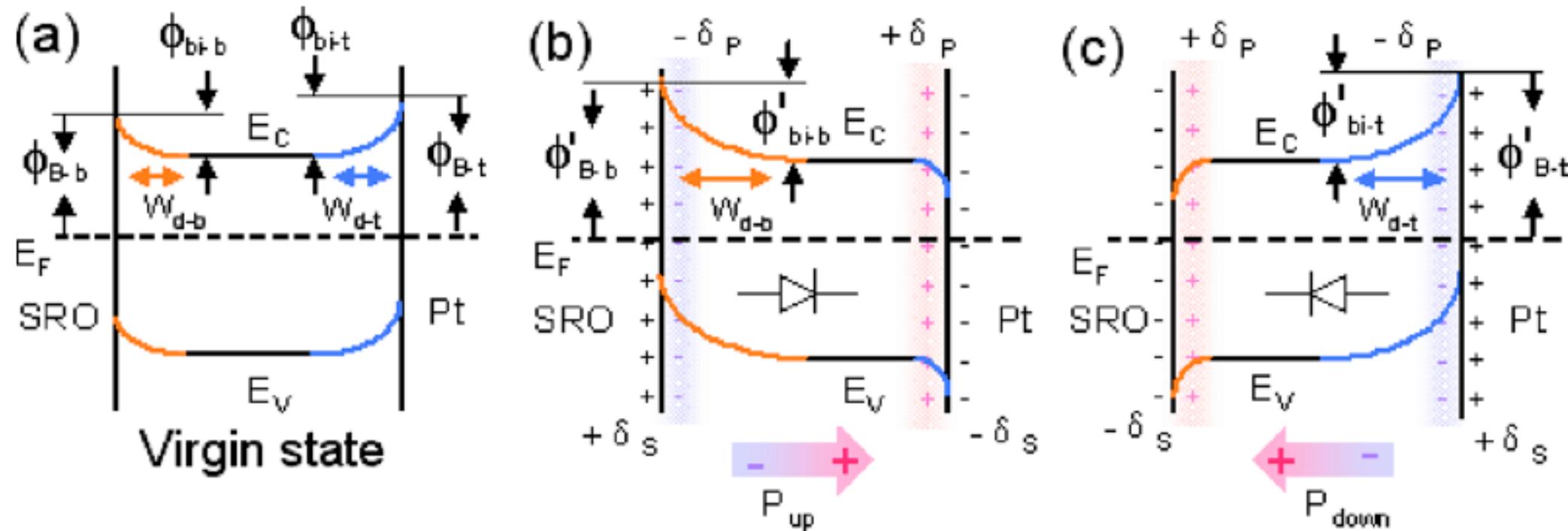
# Schottky barrier between metal and semiconductor



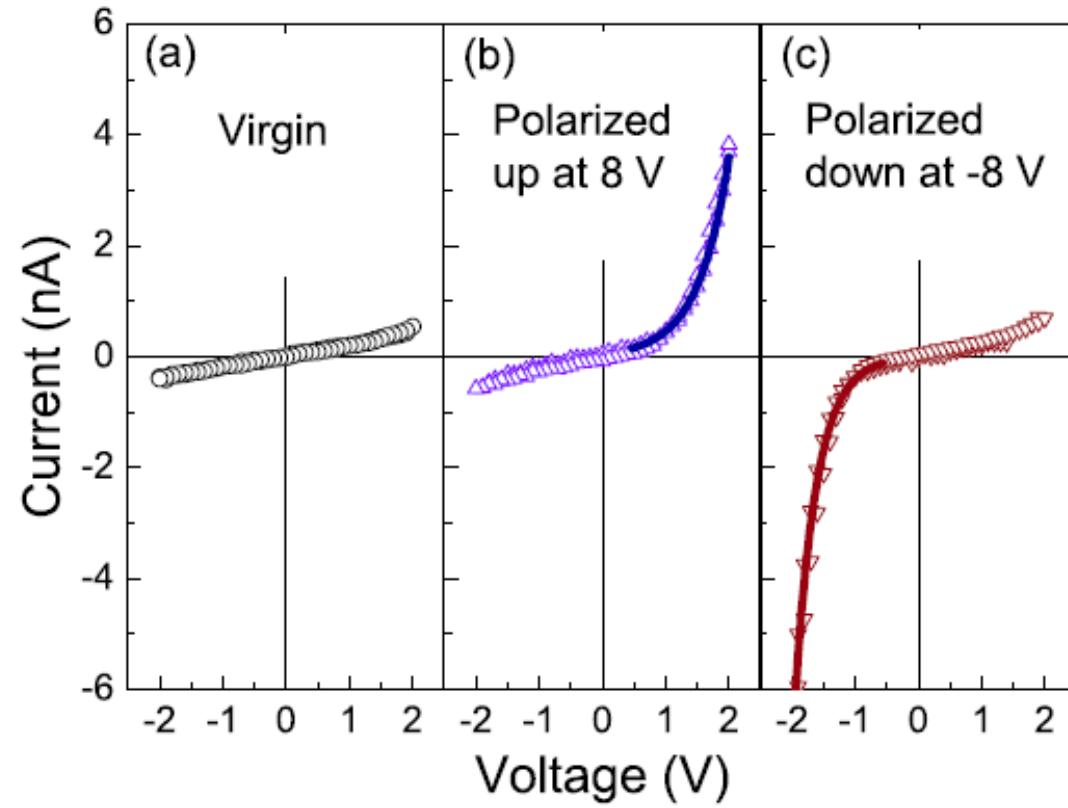
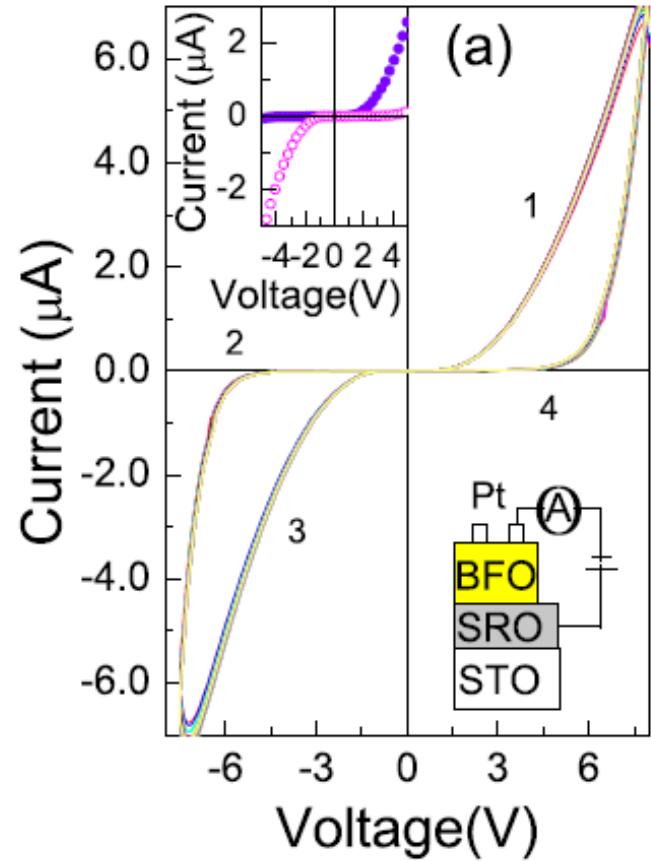
# Schottky barrier in electric field



# Switchable diode due to polarization reverse



# Experimental result



Can Wang, etc.,  
APL 98, 192901 (2011)

# Diffusion current in pn junction

- $j_D(x) = qN_D \frac{D}{L} e^{-\frac{x}{L}}$
- In pn junction with external field,  $N_D = N' - N_0$
- $N' = n_i e^{-\frac{q(V-V_D)}{k_B T}}$ , with external E
- $N' = n_i e^{-\frac{qV_D}{k_B T}}$ , without external E
- So  $j_D(x) = q \frac{D}{L} N' (e^{\frac{qV}{k_B T}} - 1)$

